

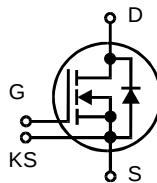
HiPerFET™ MOSFET Module

VMO 550-01F

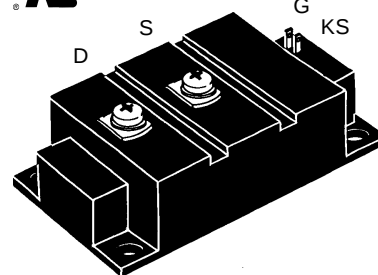
$V_{DSS} = 100 \text{ V}$
 $I_{D25} = 590 \text{ A}$
 $R_{DS(on)} = 2.1 \text{ m}\Omega$

N-Channel Enhancement Mode

Preliminary Data



 E 72873



D = Drain S = Source
KS = Kelvin Source G = Gate

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 10 \text{ k}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_S = 25^\circ\text{C}$	590	A
I_{D80}	$T_S = 80^\circ\text{C}$	440	A
I_{DM}	$T_S = 25^\circ\text{C}$ pulse width limited by T_{JM}	2360	A
P_D	$T_C = 25^\circ\text{C}$	2200	W
	$T_S = 25^\circ\text{C}$	1470	W
T_J		-40 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-40 ... +125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz $t = 1 \text{ min}$	3000	V~
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3600	
M_d	Mounting torque (M6)	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M5)	2.5-3.7/22-33	Nm/lb.in.
Weight	typical including screws	250	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 6 \text{ mA}$	100		V
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}$, $I_D = 110 \text{ mA}$	3		6 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V DC}$, $V_{DS} = 0$			$\pm 500 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$			3 mA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			12 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			2.1 m Ω

Features

- International standard package
- Direct Copper Bonded Al_2O_3 ceramic base plate
- Isolation voltage 3600 V~
- Low $R_{DS(on)}$ HDMOS™ process
- Low package inductance for high speed switching
- Kelvin Source contact for easy drive

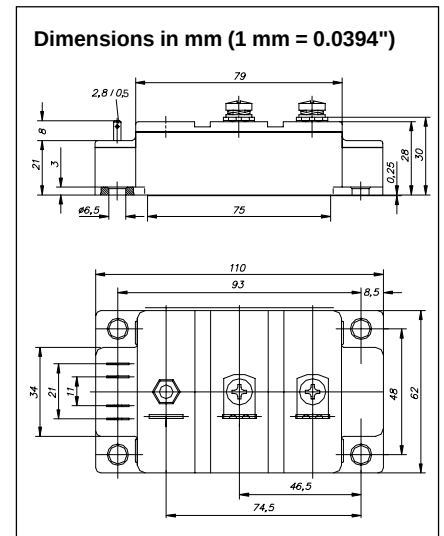
Applications

- AC motor speed control for electric vehicles
- DC servo and robot drives
- Switched-mode and resonant-mode power supplies
- DC choppers

Advantages

- Easy to mount
- Space and weight savings
- High power density
- Low losses

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ pulsed		330	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		50	nF
C_{oss}			17.6	nF
C_{rss}			8.8	nF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (external)		250	ns
t_r			500	ns
$t_{d(off)}$			800	ns
t_f			200	ns
Q_g	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		2000	nC
Q_{gs}			385	nC
Q_{gd}			940	nC
R_{thJC}	with 30 μm heat transfer paste			0.057 K/W
R_{thJS}				0.085 K/W


Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			590 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			2360 A
V_{SD}	$I_F = I_S; V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		0.9	1.2 V
t_{rr}	$I_F = I_S, -di/dt = 1000\text{ A}/\mu\text{s}, V_{DS} = 0.5 \cdot V_{DSS}$		300	ns